

ABSTRACT

A method for producing a semiconductor light-emitting device includes stacking at least a first conductive type semiconductor layer (2), an active layer (3) and a second conductive type semiconductor layer (4) on a substrate (1) to form a wafer, then forming on a side of growth surfaces of the semiconductor layers first trenches (40) exposing the first conductive type semiconductor layer, further forming second trenches (50) reaching the substrate from above the first trenches by using a laser beam, subsequently forming third trenches (60) from the substrate at the positions corresponding to the second trenches, and finally cutting the wafer into chips. The produced semiconductor chips provide an enhanced efficiency of extracting emitted light even when the end faces thereof are smooth surfaces and they allow the semiconductor layer to be cut without distorting the end faces of the chips.